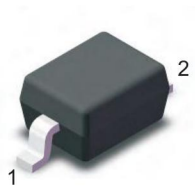
1N5817WS~1N5819WS
Schottky Barrier Diodes

Features

- High surge capability
- Low forward voltage drop
- Guarding for overvoltage protection
- Metal silicon junction, majority carrier conduction

SOD-323



1.Cathode —▷|— 2.Anode

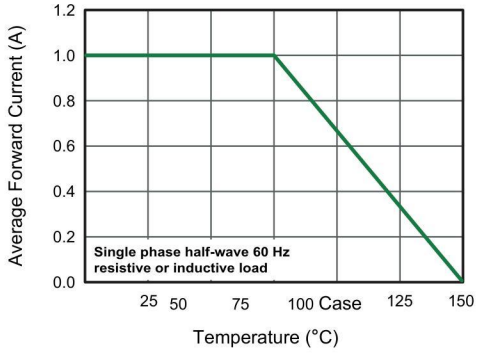
Marking Code:
1N5817WS: SJ
1N5818WS: SK
1N5819WS: SL

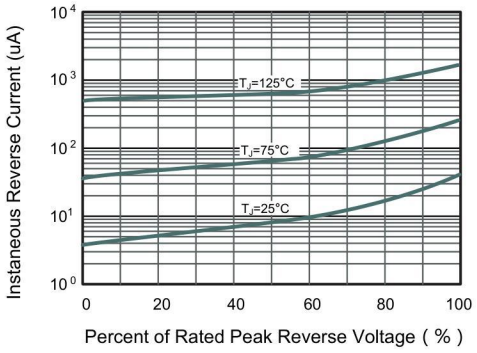
Maximum Ratings and Electrical Characteristics

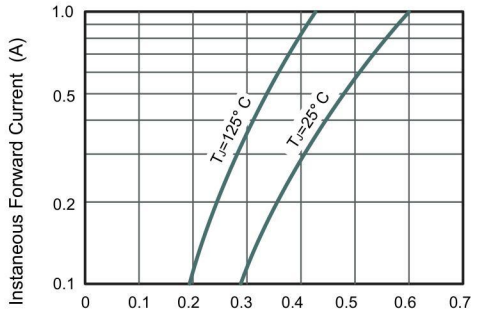
Ratings at 25℃ ambient temperature unless otherwise specified.

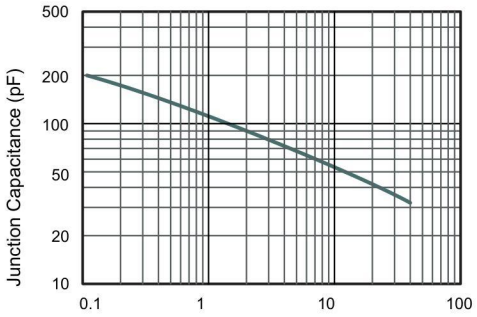
Parameter	Symbols	1N5817WS	1N5818WS	1N5819WS	Units
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	20	30	40	V
Maximum RMS Voltage	V_{RMS}	14	21	28	V
Maximum DC Blocking Voltage	V_{DC}	20	30	40	V
Maximum Average Forward Rectified Current	$I_{F(AV)}$	1.0			A
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load (JEDEC method)	I_{FSM}	9			A
Maximum Instantaneous Forward Voltage at 1 A at 3 A	V_F	 0.45 0.75	 0.55 0.875	 0.6 0.9	V
Maximum DC Reverse Current at Rated DC Blocking Voltage at T_A = 25°C at T_A = 100°C	I_R	 1 10			mA
Typical Junction Capacitance	C_j	110			pF
Operating Junction Temperature	T_J	150			°C
Storage Temperature Range	T_{STG}	-55 to +150			°C

Typical Characteristic Curves





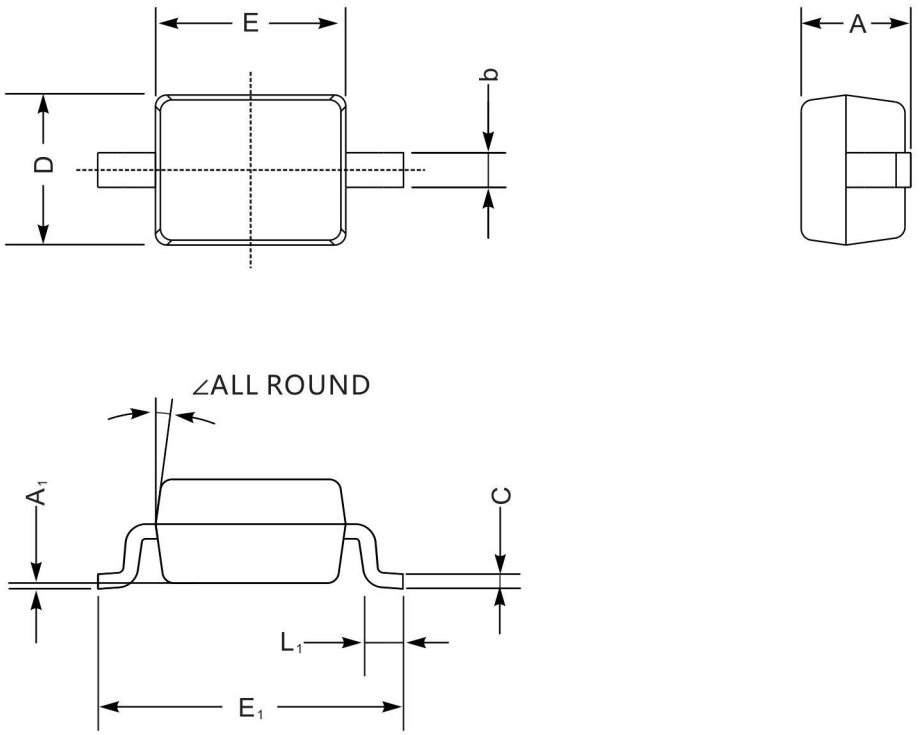




Package Outline

SOD-323

Dimensions in mm



UNIT		A	C	D	E	E_1	b	L_1	A_1	∠
mm	max	1.1	0.15	1.4	1.8	2.75	0.4	0.45	0.2	9°
	min	0.8	0.08	1.2	1.4	2.55	0.25	0.2	—	
mil	max	43	5.9	55	70	108	16	16	8	
	min	32	3.1	47	63	100	9.8	7.9	—	